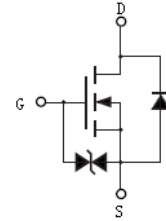




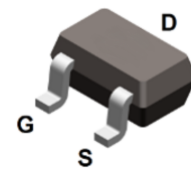
### Features

- Low on-resistance
- Low input capacitance
- Fast switching speed
- HBM: JESD22-A114-B: 2



### Typical Applications

- DC-DC converters
- Power management functions
- Battery operated systems and solid-state relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.



### Mechanical Data

- Case: SOT-323
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin-Plated Leads, Solderability-per MIL-STD-202, Method 208

**SOT-323**

### Ordering Information

| Part Number | Package | Shipping Quantity      | Marking Code |
|-------------|---------|------------------------|--------------|
| BSS138PW    | SOT-323 | 3000 pcs / Tape & Reel | 138          |

### Maximum Ratings (@ T<sub>A</sub> = 25°C unless otherwise specified)

| Parameter   | Symbol           | Value      | Unit |
|---|------------------|------------|------|
| Drain-to-Source Voltage   | V <sub>DSS</sub> | 60         | V    |
| Gate-to-Source Voltage  | V <sub>GSS</sub> | ±20        | V    |
| Continuous Drain Current (T <sub>A</sub> = 25°C) *1                 | I <sub>D</sub>   | 360        | mA   |
| Continuous Drain Current (T <sub>A</sub> = 70°C) *1                 |                  | 290        | mA   |
| Pulsed Drain Current (t <sub>p</sub> = 10μs, T <sub>A</sub> = 25°C) | I <sub>DM</sub>  | 1500       | mA   |
| Single Pulse Avalanche Energy *4                                    | E <sub>AS</sub>  | 0.2        | mJ   |
| Power Dissipation (T <sub>A</sub> = 25°C) *1                        | P <sub>D</sub>   | 350        | mW   |
| Power Dissipation (T <sub>A</sub> = 25°C) *2                        |                  | 260        | mW   |
| Operating Junction Temperature Range                                | T <sub>J</sub>   | -55 ~ +150 | °C   |
| Storage Temperature Range   | T <sub>STG</sub> | -55 ~ +150 | °C   |



### Thermal Characteristics

| Parameter  | Symbol          | Min. | Typ. | Max. | Unit                 |
|--|-----------------|------|------|------|----------------------|
| Thermal Resistance Junction-to-Case              | $R_{\theta JC}$ | -    | -    | 250  | $^{\circ}\text{C/W}$ |
| Thermal Resistance Junction-to-Air <sup>*1</sup> | $R_{\theta JA}$ | -    | 340  | 357  | $^{\circ}\text{C/W}$ |
| Thermal Resistance Junction-to-Air <sup>*2</sup> |                 | -    | -    | 480  | $^{\circ}\text{C/W}$ |

### Electrical Characteristics (@ $T_A = 25^{\circ}\text{C}$ unless otherwise specified)

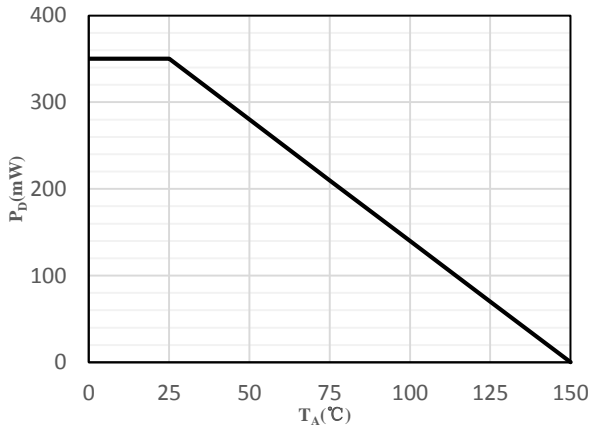
| Symbol                                    | Parameter                                | Test Condition  | Min. | Typ. | Max.     | Unit          |
|---|--|---|------|------|----------|---------------|
| <b>Static Characteristics</b>             |  |   |      |      |          |               |
| $V_{DSS}$                                 | Drain-Source Breakdown Voltage           | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$  | 60   | -    | -        | V             |
| $I_{DSS}$                                 | Zero Gate Voltage Drain Current          | $V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$   | -    | -    | 1        | $\mu\text{A}$ |
| $I_{GSS}$                                 | Gate-Body Leakage Current                | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$                                     | -    | -    | $\pm 10$ | $\mu\text{A}$ |
| <b>On Characteristics</b>                 |  |   |      |      |          |               |
| $R_{DS(ON)}$                              | Drain-Source On-resistance <sup>*3</sup> | $V_{GS} = 10\text{V}, I_D = 0.5\text{A}$  | -    | 1    | 1.6      | $\Omega$      |
|   |  | $V_{GS} = 4.5\text{V}, I_D = 0.2\text{A}$   | -    | 1.2  | 2.5      |               |
|   |  | $V_{GS} = 2.5\text{V}, I_D = 0.1\text{A}$   | -    | 1.7  | 4.5      |               |
| $V_{GS(TH)}$                              | Static Drain-Source On-resistance        | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$   | 0.8  | 1    | 1.5      | V             |
| $R_G$                                     | Gate Resistance                          | $V_{GS} = 0\text{V}, f = 1\text{MHz}$   | -    | 48   | -        | $\Omega$      |
| <b>Dynamic Characteristics</b>            |  |   |      |      |          |               |
| $C_{ISS}$                                 | Input Capacitance                        | $V_{GS} = 0\text{V}$<br>$V_{DS} = 25\text{V}$<br>$f = 1.0\text{MHz}$              | -    | 32   | -        | pF            |
| $C_{OSS}$                                 | Output Capacitance                       |   | -    | 6    | -        |               |
| $C_{RSS}$                                 | Reverse Transfer Capacitance             |   | -    | 3    | -        |               |
| <b>Switching Characteristics</b>          |  |   |      |      |          |               |
| $t_{d(on)}$                               | Turn-on Delay Time <sup>*5</sup>         | $V_{DD} = 25\text{V}, I_D = 0.36\text{A}$<br>$V_{GS} = 10\text{V}, R_G = 6\Omega$ | -    | 2.2  | -        | ns            |
| $t_r$                                     | Turn-on Rise Time <sup>*5</sup>          |   | -    | 19.2 | -        |               |
| $t_{d(off)}$                              | Turn-Off Delay Time <sup>*5</sup>        |   | -    | 6.2  | -        |               |
| $t_f$                                     | Turn-Off Fall Time <sup>*5</sup>         |   | -    | 23   | -        |               |
| $Q_G$                                     | Total Gate-Charge                        | $V_{DS} = 25\text{V}$<br>$V_{GS} = 10\text{V}$<br>$I_D = 0.2\text{A}$             | -    | 4    | -        | nC            |
| $Q_{GS}$                                  | Gate to Source Charge                    |   | -    | 0.5  | -        |               |
| $Q_{GD}$                                  | Gate to Drain (Miller) Charge            |   | -    | 0.4  | -        |               |
| <b>Source-Drain Diode Characteristics</b> |  |   |      |      |          |               |
| $V_{SD}$                                  | Diode Forward Voltage <sup>*3</sup>      | $I_S = 0.5\text{A}, V_{GS} = 0\text{V}$   | -    | 0.89 | 1.4      | V             |
| $t_{rr}$                                  | Reverse Recovery Time                    | $I_F = 1\text{A}, V_{GS} = 0\text{V}$   | -    | 15   | -        | ns            |
| $Q_{rr}$                                  | Reverse Recovery Charge                  | $dI_F/dt = 100\text{A}/\mu\text{s}$   | -    | 8    | -        | nC            |

#### Notes:

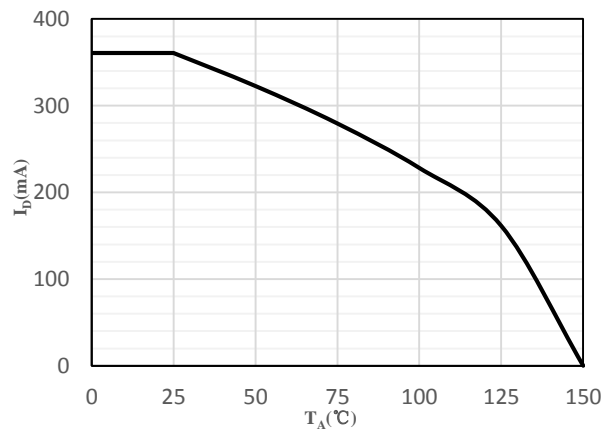
- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper
- The data tested by surface mounted on a minimum recommended FR-4 board
- The data tested by pulsed, pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$
- The  $E_{AS}$  data shows Max. rating. The test condition is  $V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, L = 0.5\text{mH}$
- Guaranteed by design, not subject to production



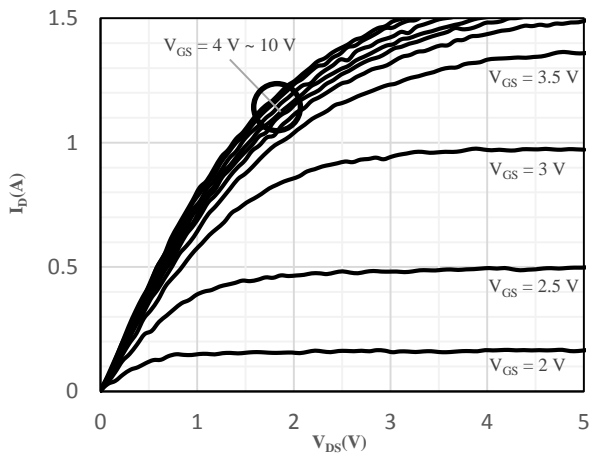
### Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)



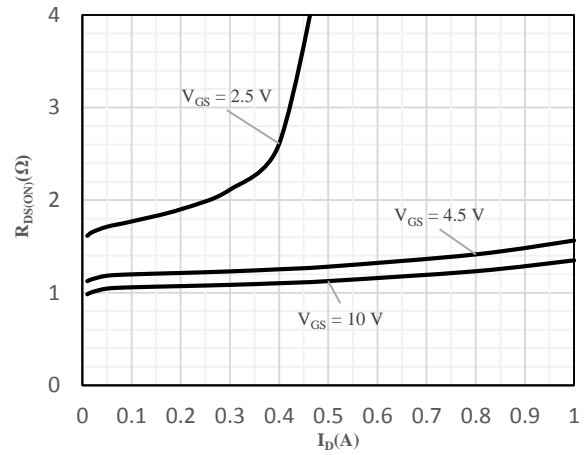
**Fig 1 Power Dissipation**



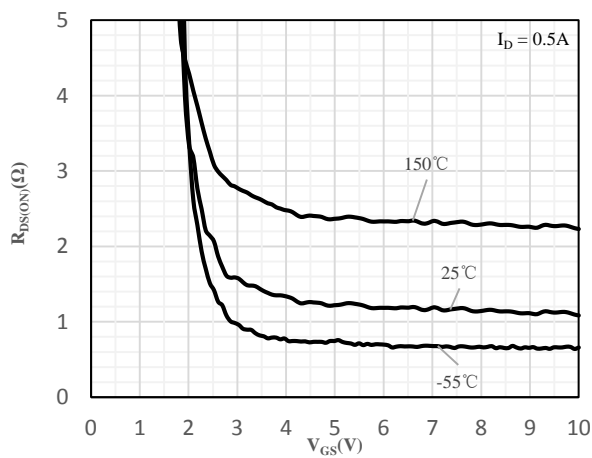
**Fig 2 Drain Current**



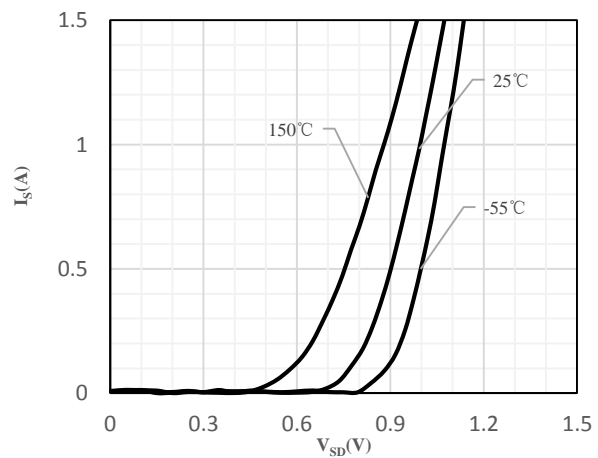
**Fig 3 Typical Output Characteristics**



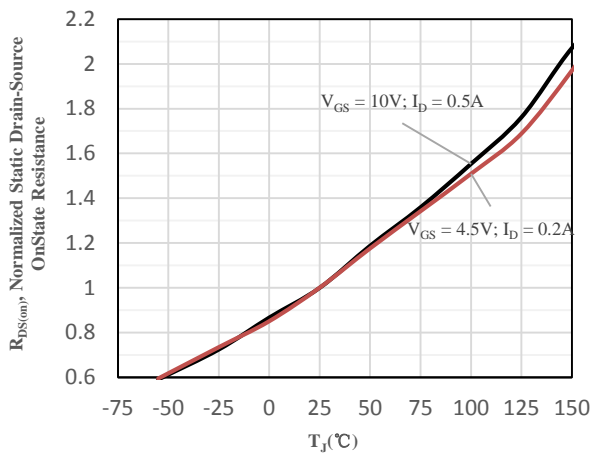
**Fig 4 On-Resistance vs. Drain Current and Gate Voltage**



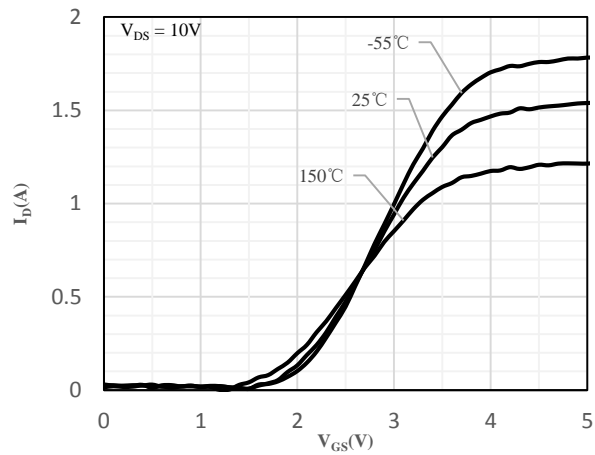
**Fig 5 On-Resistance vs. Gate-Source Voltage**



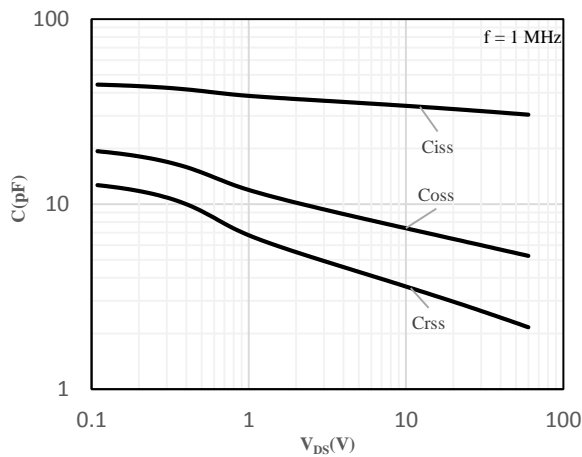
**Fig 6 Body-Diode Characteristics**



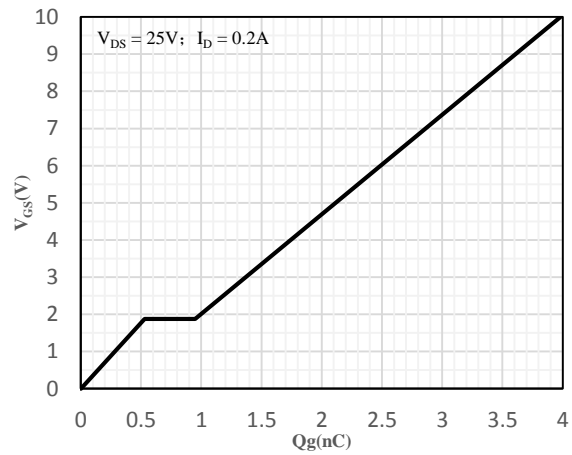
**Fig 7 Normalized On-Resistance vs. Junction Temperature**



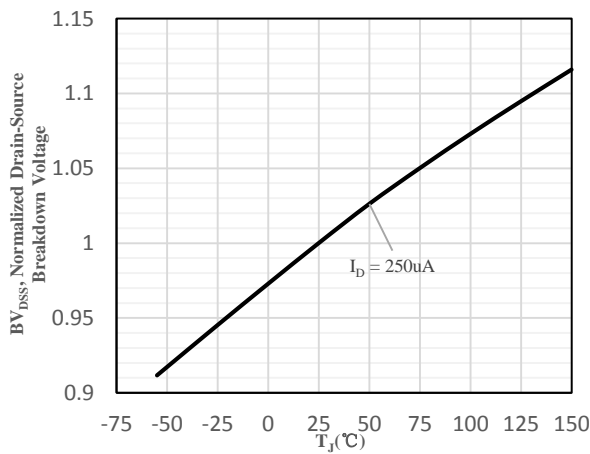
**Fig 8 Transfer Characteristics**



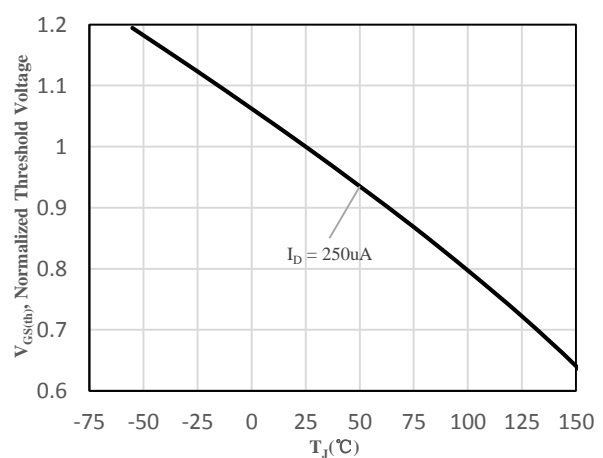
**Fig 9 Capacitance Characteristics**



**Fig 10 Gate-Charge Characteristics**



**Fig 11 Normalized Breakdown Voltage vs. Junction Temperature**



**Fig 12 Normalized  $V_{GS(th)}$  vs. Junction Temperature**

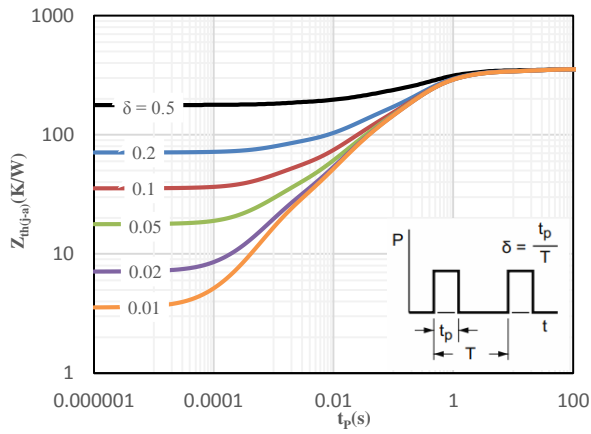


Fig 13 Safe Operation Area

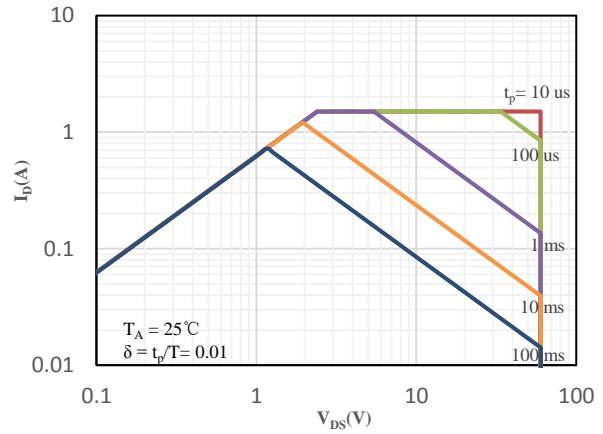
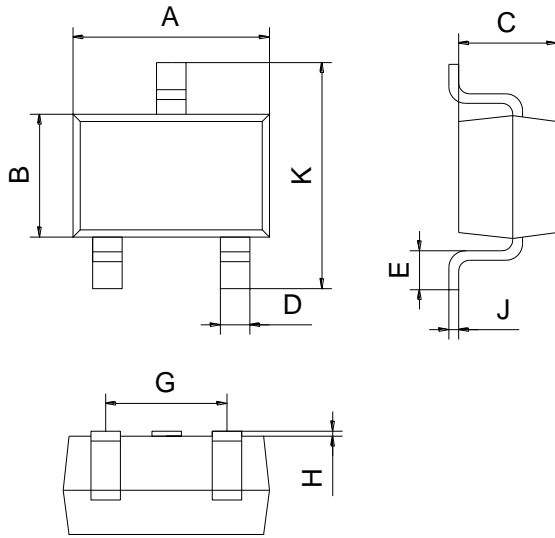


Fig 14 Maximum transient thermal impedance



### Package Outline Dimensions (Unit: mm)



| SOT-323   |      |      |
|-----------|------|------|
| Dimension | Min. | Max. |
| A         | 2.00 | 2.20 |
| B         | 1.15 | 1.35 |
| C         | 0.90 | 1.10 |
| D         | 0.15 | 0.35 |
| E         | 0.25 | 0.40 |
| G         | 1.20 | 1.40 |
| H         | 0.02 | 0.10 |
| J         | 0.05 | 0.15 |
| K         | 2.20 | 2.40 |

### Mounting Pad Layout (Unit: mm)

#### SOT-323

